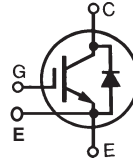




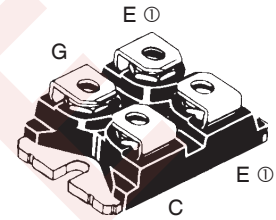
XPT™ 650V GenX4™ IXXN110N65B4H1 w/ Sonic Diode

Extreme Light Punch Through
IGBT for 10-30kHz Switching



$$\begin{aligned} V_{CES} &= 650V \\ I_{C110} &= 110A \\ V_{CE(sat)} &\leq 2.10V \\ t_{fi(typ)} &= 43ns \end{aligned}$$

SOT-227B, miniBLOC
E153432



G = Gate, C = Collector, E = Emitter
① either emitter terminal can be used as Main or Kelvin Emitter

Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ\text{C to } 175^\circ\text{C}$	650	V
V_{CGR}	$T_J = 25^\circ\text{C to } 175^\circ\text{C}, R_{GE} = 1M\Omega$	650	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ\text{C}$ (Chip Capability)	230	A
I_{C25}	Terminal Current Limit	200	A
I_{C110}	$T_C = 110^\circ\text{C}$	110	A
I_{F110}	$T_C = 110^\circ\text{C}$	70	A
I_{CM}	$T_C = 25^\circ\text{C}, 1\text{ms}$	650	A
SSOA (RBSOA)	$V_{GE} = 15V, T_{VJ} = 150^\circ\text{C}, R_G = 2\Omega$ Clamped Inductive Load	$I_{CM} = 220$ @ $V_{CE} \leq V_{CES}$	A
t_{sc} (SCSOA)	$V_{GE} = 15V, V_{CE} = 360V, T_J = 150^\circ\text{C}$ $R_G = 82\Omega$, Non Repetitive	10	μs
P_C	$T_C = 25^\circ\text{C}$	750	W
T_J		-55 ... +175	$^\circ\text{C}$
T_{JM}		175	$^\circ\text{C}$
T_{stg}		-55 ... +175	$^\circ\text{C}$
V_{ISOL}	50/60Hz $I_{ISOL} \leq 1\text{mA}$	$t = 1\text{min}$ $t = 1\text{s}$	2500 3000 V~ V~
M_d	Mounting Torque Terminal Connection Torque	1.5/13 1.3/11.5	Nm/lb.in. Nm/lb.in.
Weight		30	g

Features

- International Standard Package
- miniBLOC, with Aluminium Nitride Isolation
- 2500V~ Isolation Voltage
- Anti-Parallel Sonic Diode
- Optimized for 10-30kHz Switching
- Square RBSOA
- Short Circuit Capability
- High Current Handling Capability

Advantages

- High Power Density
- Low Gate Drive Requirement

Applications

- Power Inverters
- UPS
- Motor Drives
- SMPS
- PFC Circuits
- Battery Chargers
- Welding Machines
- Lamp Ballasts

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{CES}	$I_C = 250\mu\text{A}, V_{GE} = 0V$	650		V
$V_{GE(th)}$	$I_C = 250\mu\text{A}, V_{CE} = V_{GE}$	4.0		6.5 V
I_{CES}	$V_{CE} = V_{CES}, V_{GE} = 0V$ $T_J = 150^\circ\text{C}$			50 μA 3 mA
I_{GES}	$V_{CE} = 0V, V_{GE} = \pm 20V$			± 100 nA
$V_{CE(sat)}$	$I_C = 110A, V_{GE} = 15V$, Note 1 $T_J = 150^\circ\text{C}$		1.72 2.05	V V

Symbol Test Conditions

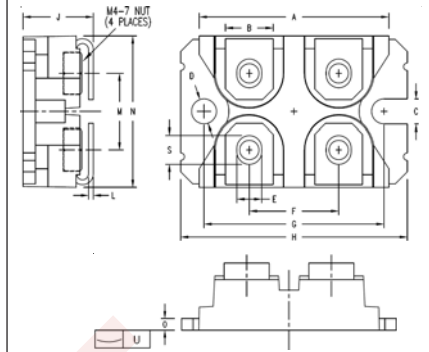
(T_J = 25°C Unless Otherwise Specified)

Characteristic Values

Min. Typ. Max.

g_{fs}	I _C = 60A, V _{CE} = 10V, Note 1	30	52	S
C_{ies}	V _{CE} = 25V, V _{GE} = 0V, f = 1MHz		3650	pF
C_{oes}			470	pF
C_{res}			80	pF
Q_g	I _C = 110A, V _{GE} = 15V, V _{CE} = 0.5 • V _{CES}		183	nC
Q_{ge}			32	nC
Q_{gc}			83	nC
t_{d(on)}	Inductive load, T _J = 25°C I _C = 55A, V _{GE} = 15V V _{CE} = 400V, R _G = 2Ω Note 2		26	ns
t_{ri}			40	ns
E_{on}			2.20	mJ
t_{d(off)}			146	ns
t_{fi}			43	ns
E_{off}			1.05	mJ
t_{d(on)}	Inductive load, T _J = 150°C I _C = 55A, V _{GE} = 15V V _{CE} = 400V, R _G = 2Ω Note 2		25	ns
t_{ri}			40	ns
E_{on}			3.00	mJ
t_{d(off)}			140	ns
t_{fi}			110	ns
E_{off}			2.16	mJ
R_{thJC}				0.20 °C/W
R_{thCS}		0.05		°C/W

SOT-227B miniBLOC (IXXN)



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.224	1.260	31.10	32.00
B	.303	.327	7.70	8.30
C	.161	.173	4.10	4.40
D	.161	.173	4.10	4.40
E	.161	.173	4.10	4.40
F	.587	.598	14.90	15.20
G	1.181	1.201	30.00	30.50
H	1.488	1.508	37.80	38.30
J	.461	.484	11.70	12.30
L	.030	.033	0.75	0.85
M	.492	.512	12.50	13.00
N	.984	1.004	25.00	25.50
O	.075	.087	1.90	2.20
S	.181	.193	4.60	4.90
U	.000	.005	0.00	0.13

Reverse Sonic Diode (FRD)

Symbol Test Conditions

(T_J = 25°C Unless Otherwise Specified)

Characteristic Values

Min. Typ. Max.

V_F	I _F = 100A, V _{GE} = 0V, Note 1	T _J = 150°C	1.7	2.3	V
			1.8		V
I_{RM}	I _F = 100A, V _{GE} = 0V, -di _F /dt = 1500A/μs, V _R = 300V	T _J = 150°C	95		A
t_{rr}			100		ns
R_{thJC}				0.42	°C/W

Notes:

1. Pulse test, t ≤ 300μs, duty cycle, d ≤ 2%.
2. Switching times & energy losses may increase for higher V_{CE}(clamp), T_J or R_G.

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
4,860,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

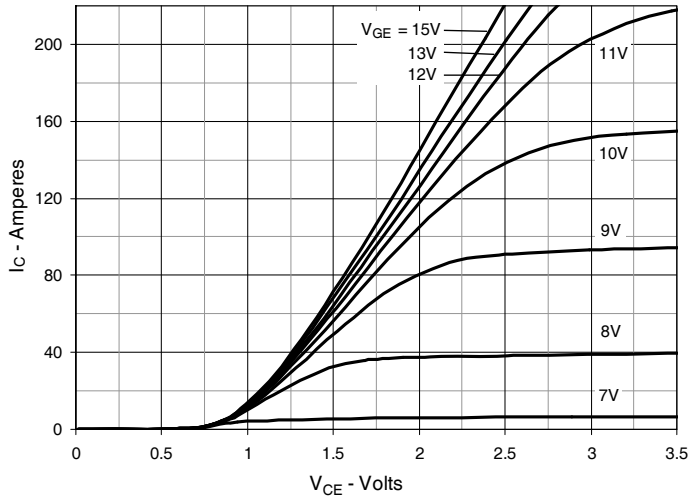
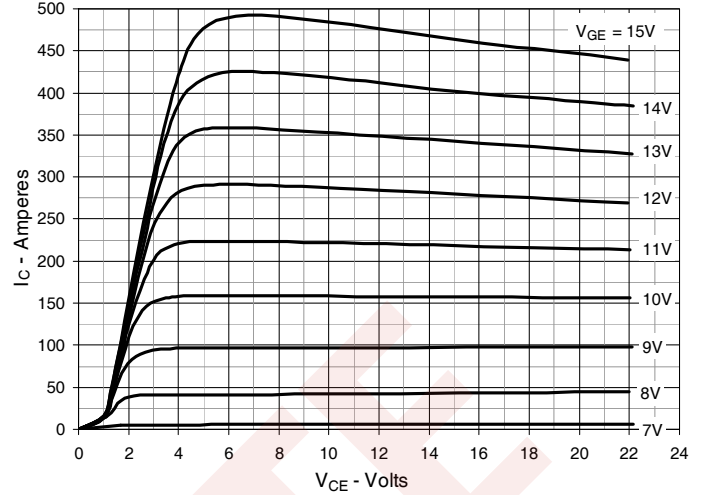
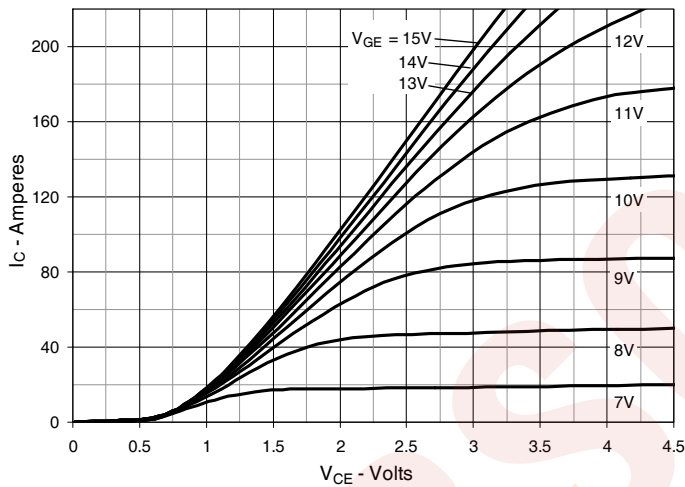
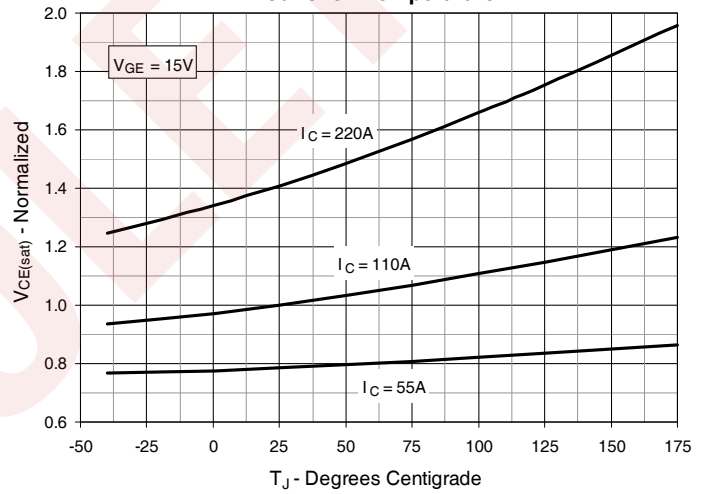
Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$ Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$ Fig. 3. Output Characteristics @ $T_J = 150^\circ\text{C}$ Fig. 4. Dependence of $V_{CE(sat)}$ on Junction Temperature

Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage

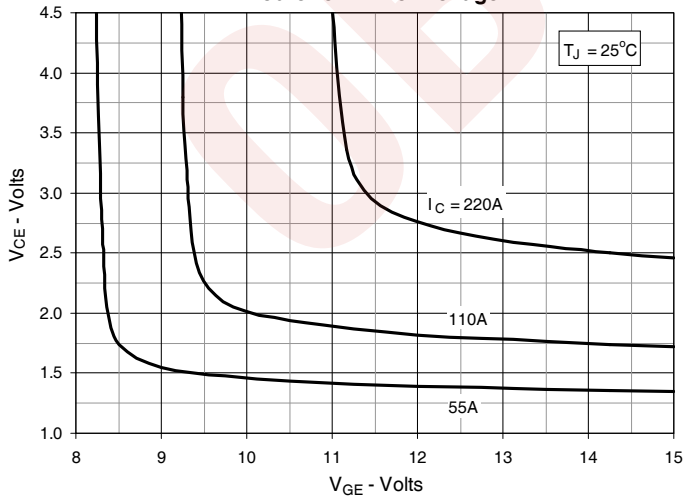


Fig. 6. Input Admittance

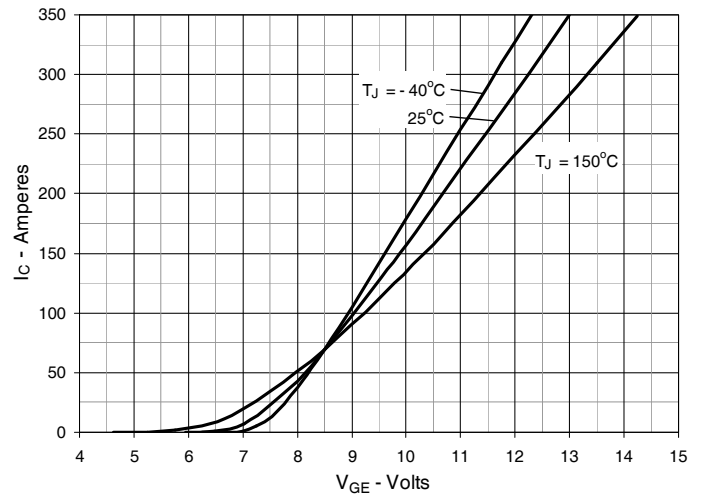


Fig. 7. Transconductance

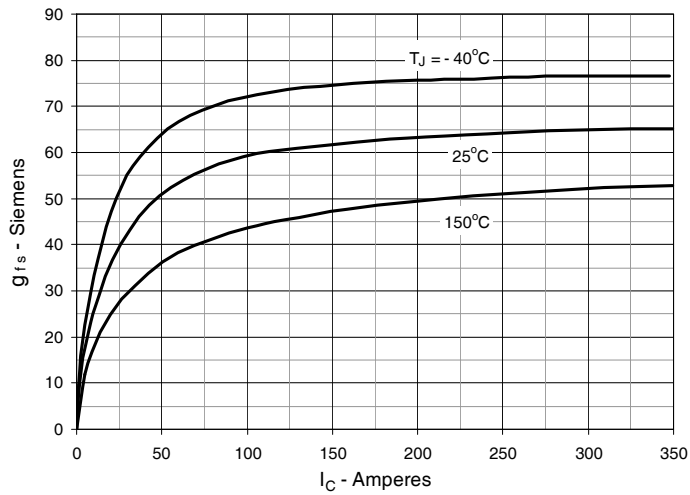


Fig. 8. Gate Charge

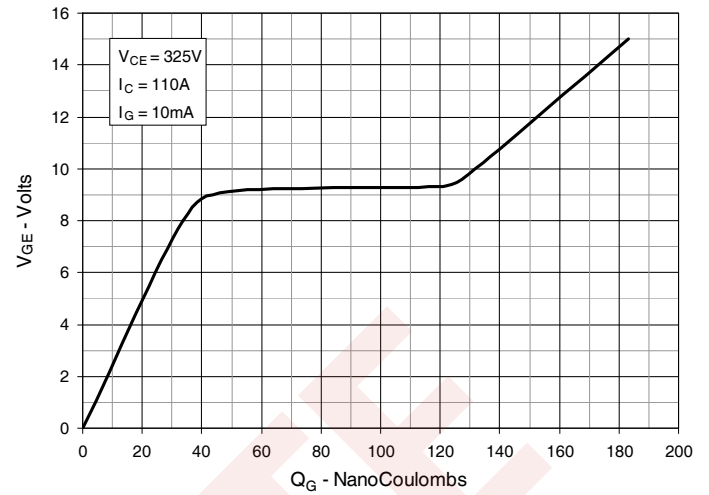


Fig. 9. Capacitance

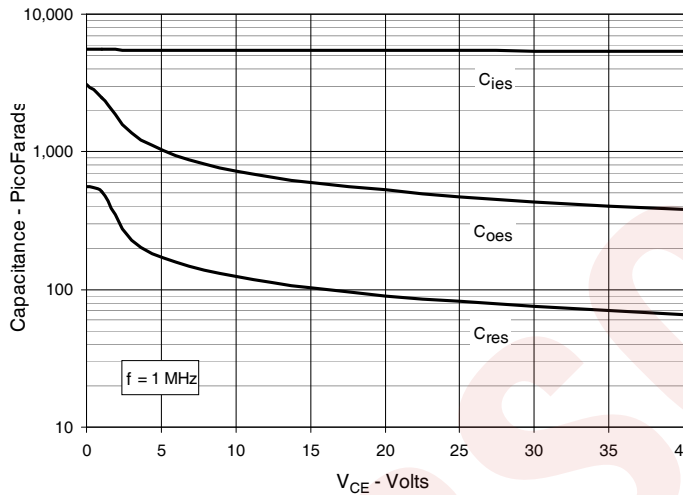


Fig. 10. Reverse-Bias Safe Operating Area

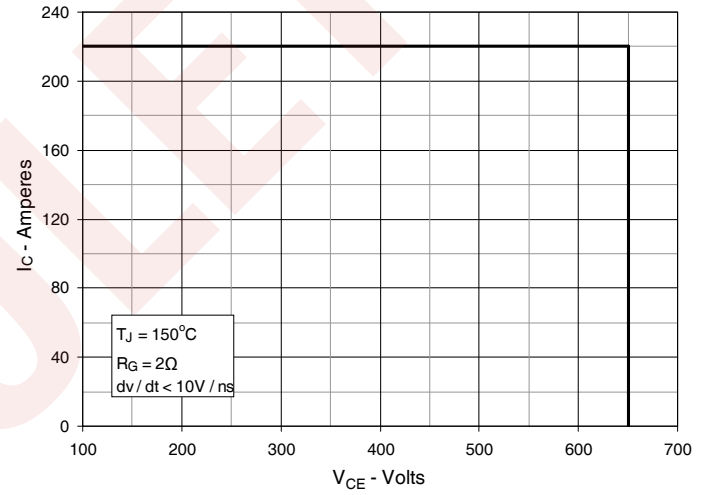


Fig. 11. Maximum Transient Thermal Impedance (IGBT)

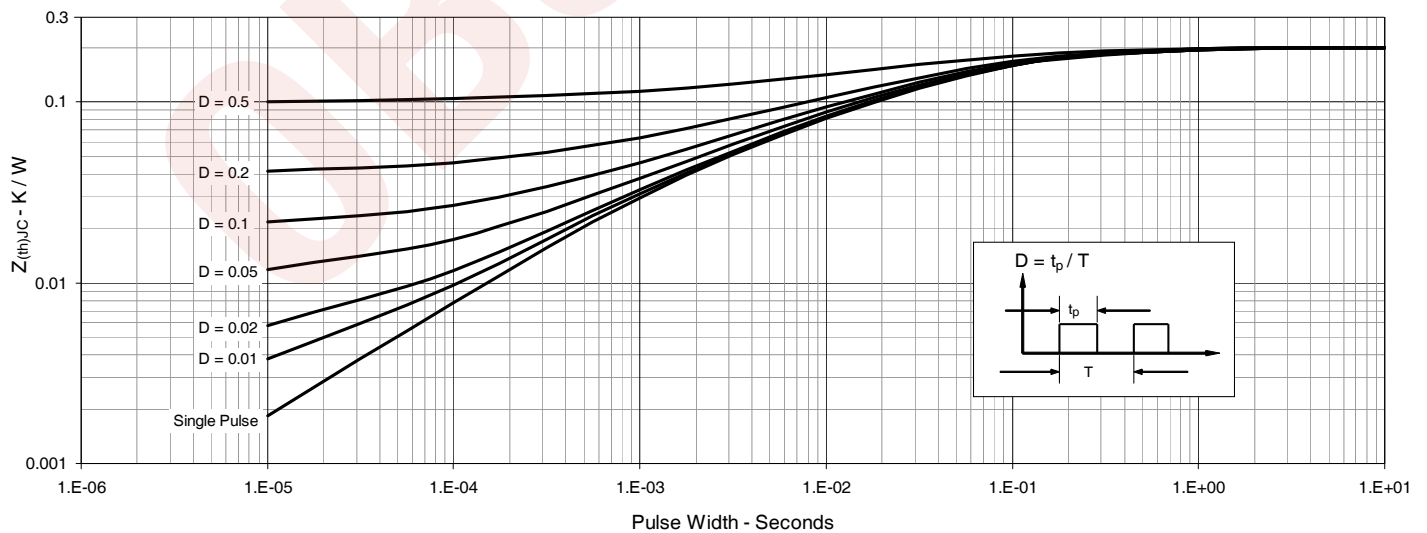


Fig. 12. Inductive Switching Energy Loss vs. Gate Resistance

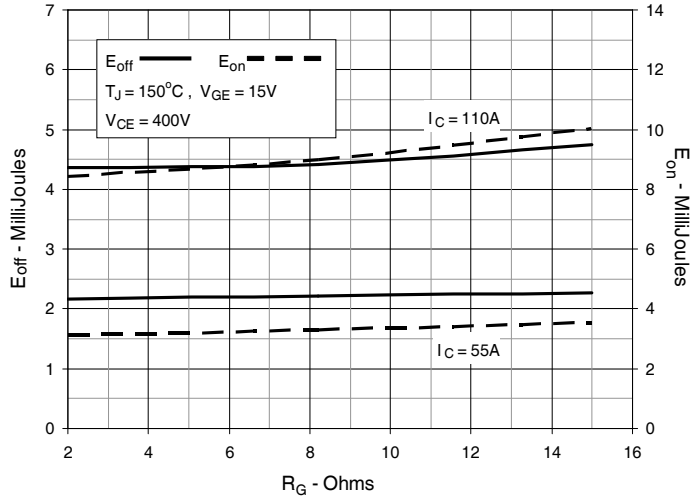


Fig. 13. Inductive Switching Energy Loss vs. Collector Current

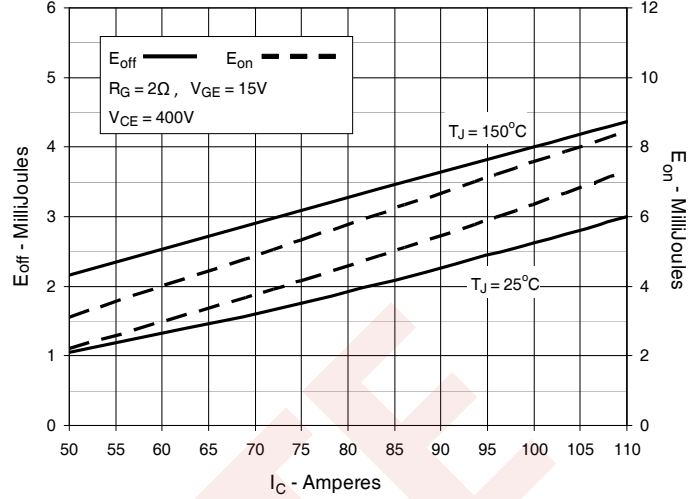


Fig. 14. Inductive Switching Energy Loss vs. Junction Temperature

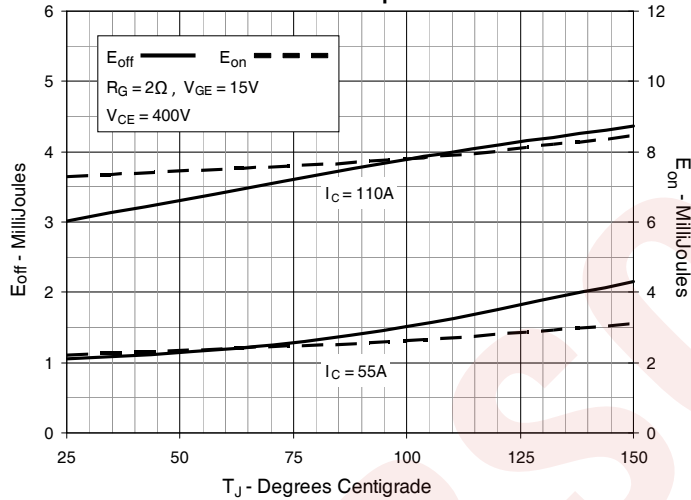


Fig. 15. Inductive Turn-off Switching Times vs. Gate Resistance

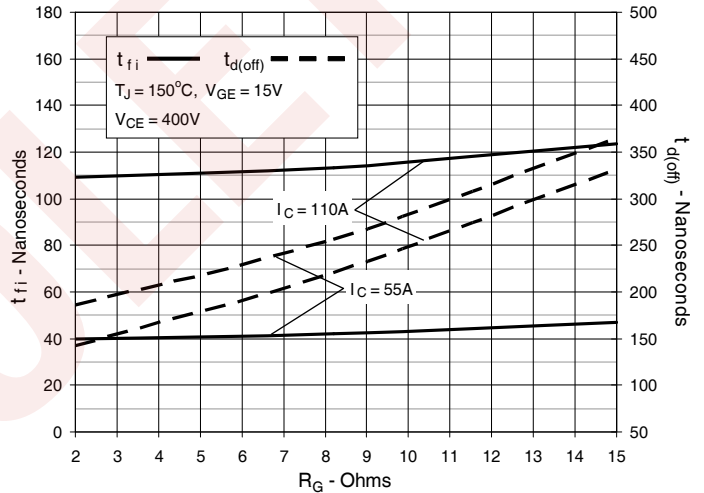


Fig. 16. Inductive Turn-off Switching Times vs. Collector Current

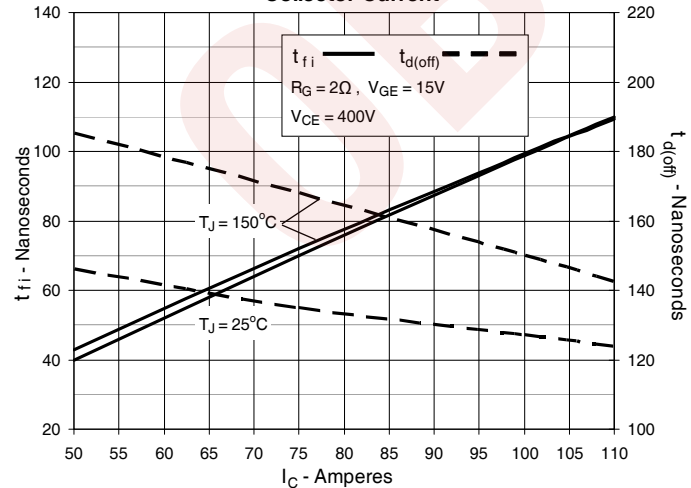


Fig. 17. Inductive Turn-off Switching Times vs. Junction Temperature

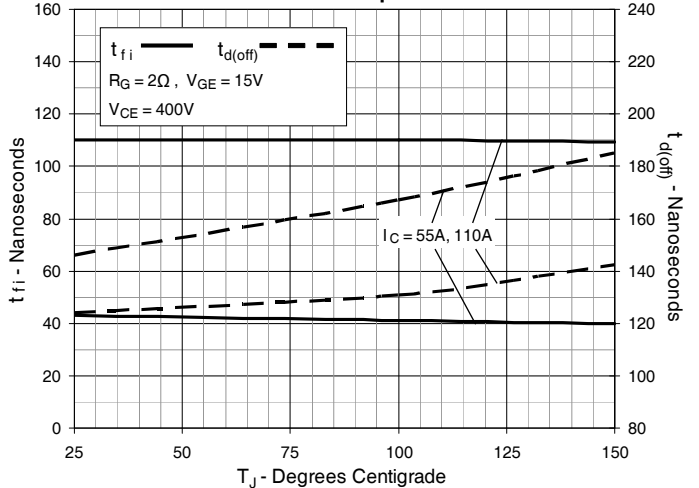


Fig. 18. Inductive Turn-on Switching Times vs. Gate Resistance

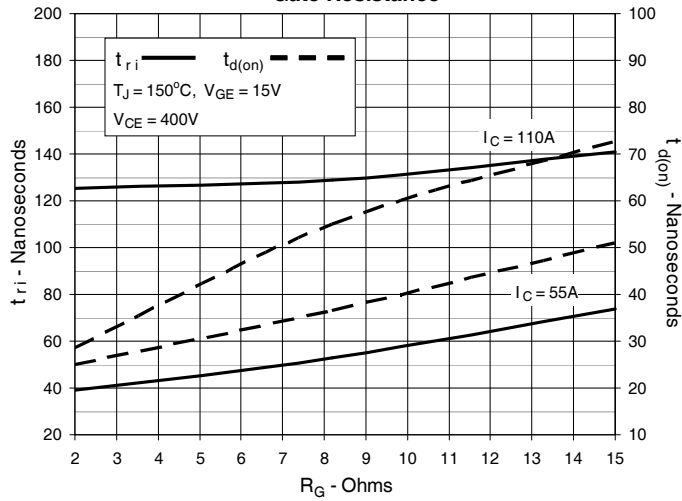


Fig. 19. Inductive Turn-on Switching Times vs. Collector Current

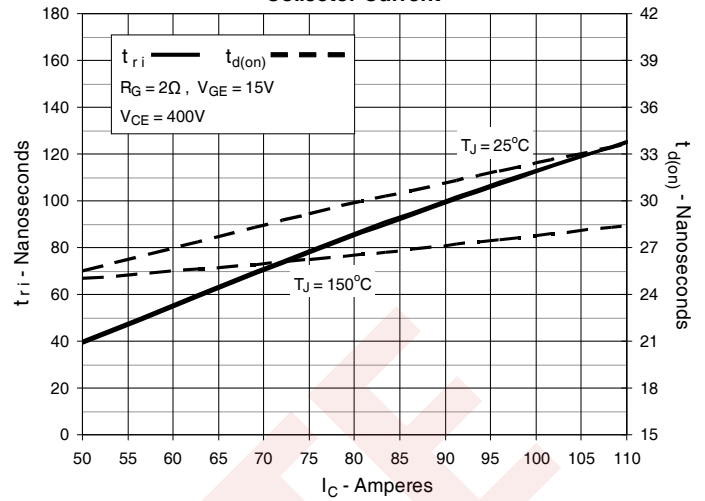


Fig. 20. Inductive Turn-on Switching Times vs. Junction Temperature

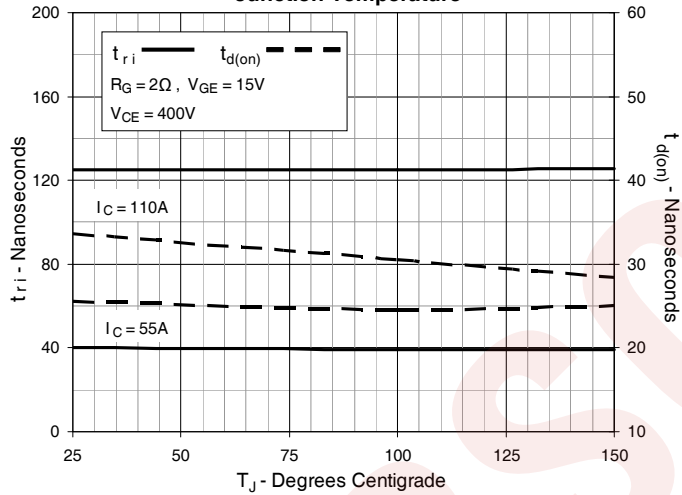


Fig. 21. Typ. Forward characteristics

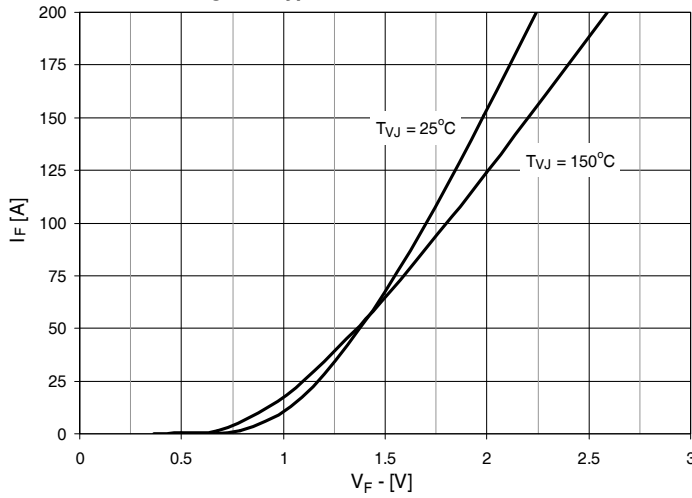
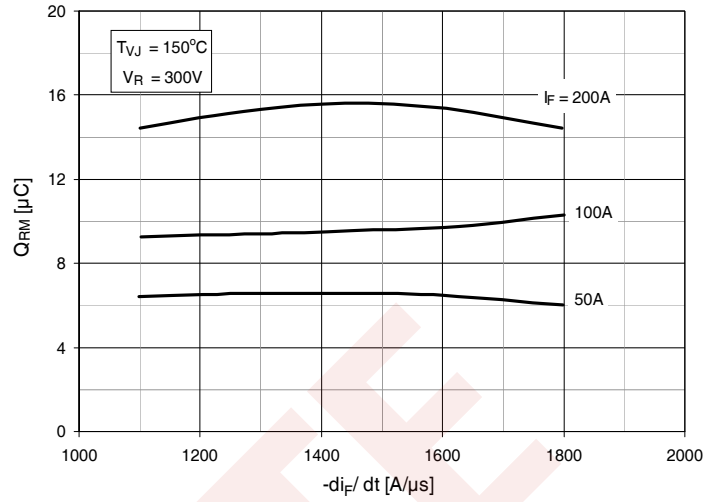
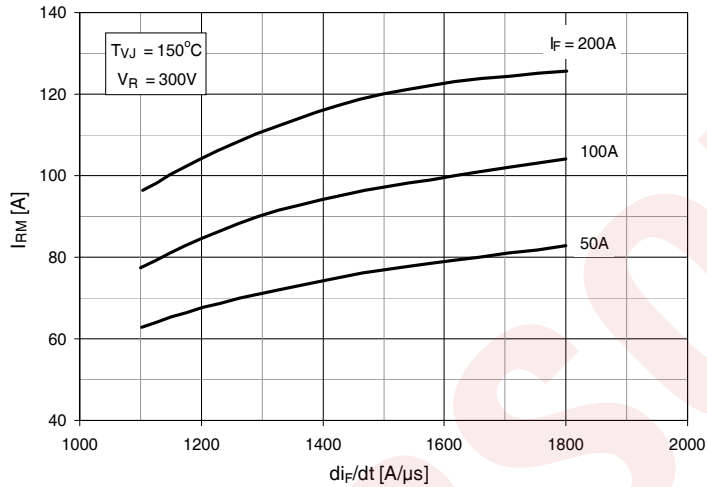
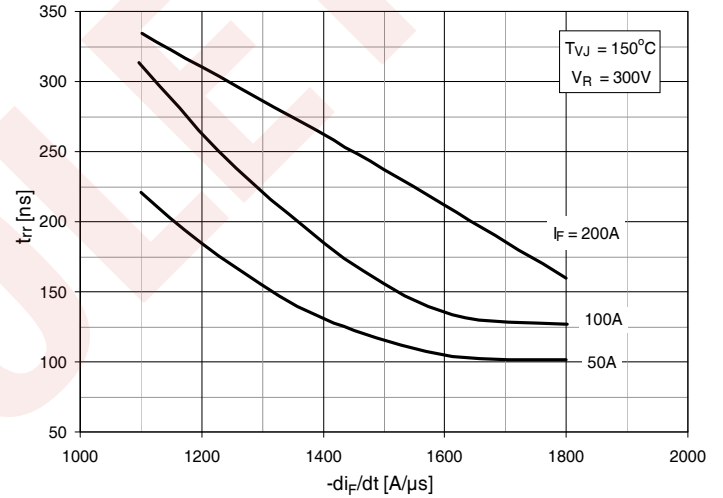
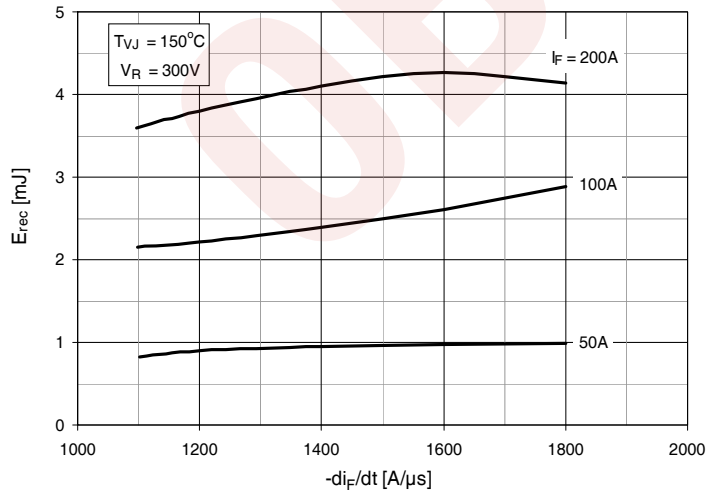
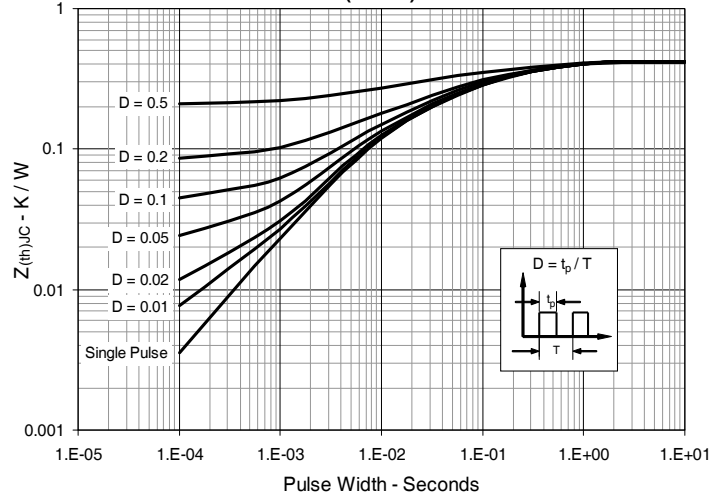
Fig. 22. Typ. Reverse Recovery Charge Q_{rr} vs. $-di_F/dt$ Fig. 23. Typ. Peak Reverse Current I_{RM} vs. $-di_F/dt$ Fig. 24. Typ. Recovery Time t_{rr} vs. $-di_F/dt$ Fig. 25. Typ. Recovery Energy E_{rec} vs. $-di_F/dt$ 

Fig. 26. Maximum Transient Thermal Impedance (Diode)



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